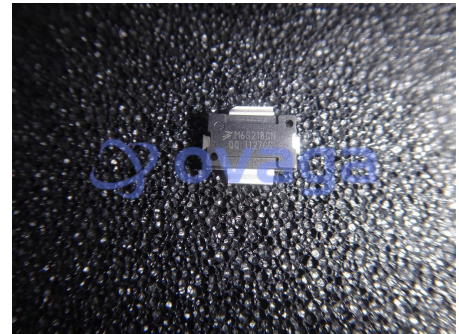


RF Power Field Effect Transistors,MOSFET HV6 2GHZ 10W

Manufacturers	NXP Semiconductor
Package/Case	TO-270
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for MRF6S20010GNR1 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

MRF6S20010GNR1 is a high-power RF transistor manufactured by NXP Semiconductors.

Features

Operating frequency: 1920 - 1990 MHz

Output Power: 10 W

Efficiency: 57%

Gain: 12 dB

Voltage: 32 V

Package: OM-780-4

Application

AFT05MS004NT1

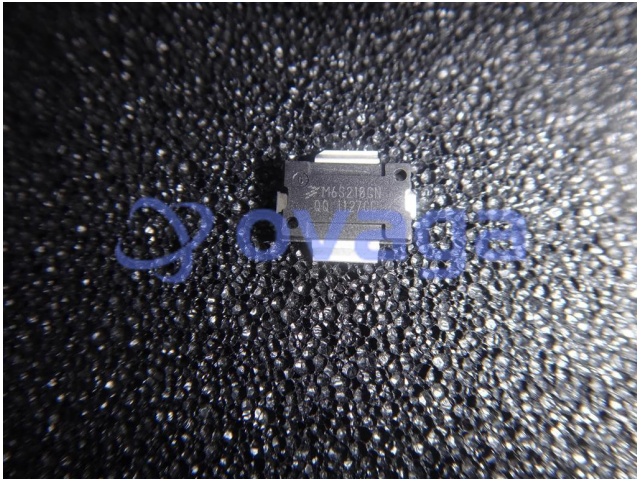
BLC9G20L-160AV

FLL57MK-A

PTFA091001FV5

QPD0009L

SPF-2860Z



Related Products



[MRFE6S9125NR1](#)

NXP Semiconductor
TO-270



[MRF9030LR1](#)

NXP Semiconductor
NI-360-3



[MRF8P20100HSR3](#)

NXP Semiconductor
NI-780S-4



[MRF8P20160HSR3](#)

NXP Semiconductor
NI-780S-4



[MRF6VP2600HR6](#)

NXP Semiconductor
NI-1230



[MRF6V2300NBR1](#)

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TO-272



[MRF6VP2600H](#)

NXP Semiconductor
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[MRF374A](#)

NXP Semiconductor
NI-650